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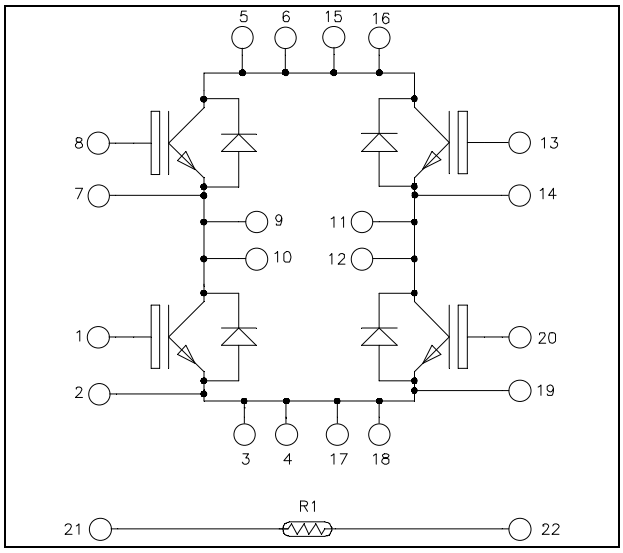
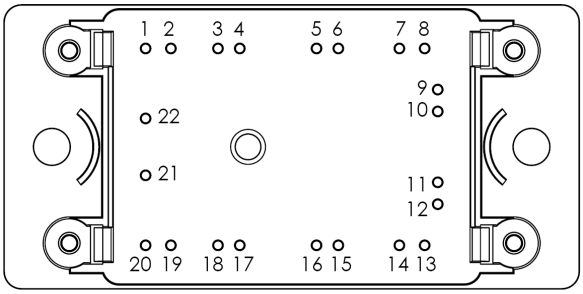
APTGLQ25H120T2G

Full - Bridge
High speed Trench + Field Stop
IGBT4 Power Module

V_{CES} = 1200V
I_C = 25A @ Tc = 80°C





Pins 5/6/15/16 ; 3/4/17/18 ; 9/10 ; 11/12 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- ***High speed Trench + Field Stop IGBT 4 Technology***
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	50	A
		T_C = 80°C	25	
I_{CM}	Pulsed Collector Current	T_C = 25°C	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation		165	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				50	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V I_C = 25A	T_j = 25°C	1.78	2.05	2.42	V
			T_j = 150°C		2.6		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 0.85 mA		5.3	5.8	6.3	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				150	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			1430		pF
C_{oes}	Output Capacitance				95		
C_{res}	Reverse Transfer Capacitance				75		
Q_G	Gate charge	V_{GE} = 15V, I_C = 25A V_{CE} = 960V			115		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 25A R_G = 19Ω			27		ns
T_r	Rise Time				41		
$T_{d(off)}$	Turn-off Delay Time				277		
T_f	Fall Time				17		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 25A R_G = 19Ω			26		ns
T_r	Rise Time				35		
$T_{d(off)}$	Turn-off Delay Time				347		
T_f	Fall Time				50		
E_{on}	Turn on Energy	V_{GE} = ±15V V_{Bus} = 600V I_C = 25A R_G = 19Ω	T_j = 150°C		2.4		mJ
E_{off}	Turn off Energy		T_j = 150°C		1.4		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 600V t_p≤10µs ; T_j = 150°C			90		A
R_{thJC}	Junction to Case Thermal Resistance					0.9	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	V_R=1200V				100	µA
I_F	DC Forward Current		Tc = 80°C		25		A
V_F	Diode Forward Voltage	I_F = 25A			2.6	3.3	V
		I_F = 50A			3.2		
		I_F = 25A	T_j = 125°C		1.8		
t_{rr}	Reverse Recovery Time	I_F = 25A V_R = 667V di/dt =200A/µs	T_j = 25°C		320		ns
			T_j = 125°C		360		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		480		nC
			T_j = 125°C		1800		
R_{thJC}	Junction to Case Thermal Resistance					1.4	°C/W

Temperature sensor NTC

Symbol	*Characteristic*	*Min*	*Typ*	*Max*	*Unit*
R_{25}	Resistance @ 25°C		22		kΩ
$\Delta R_{25}/R_{25}$	Resistance tolerance			5	%
$\Delta B/B$	Beta tolerance			3	
$B_{25/100}$	T_{25} = 298.16 K		3980		K

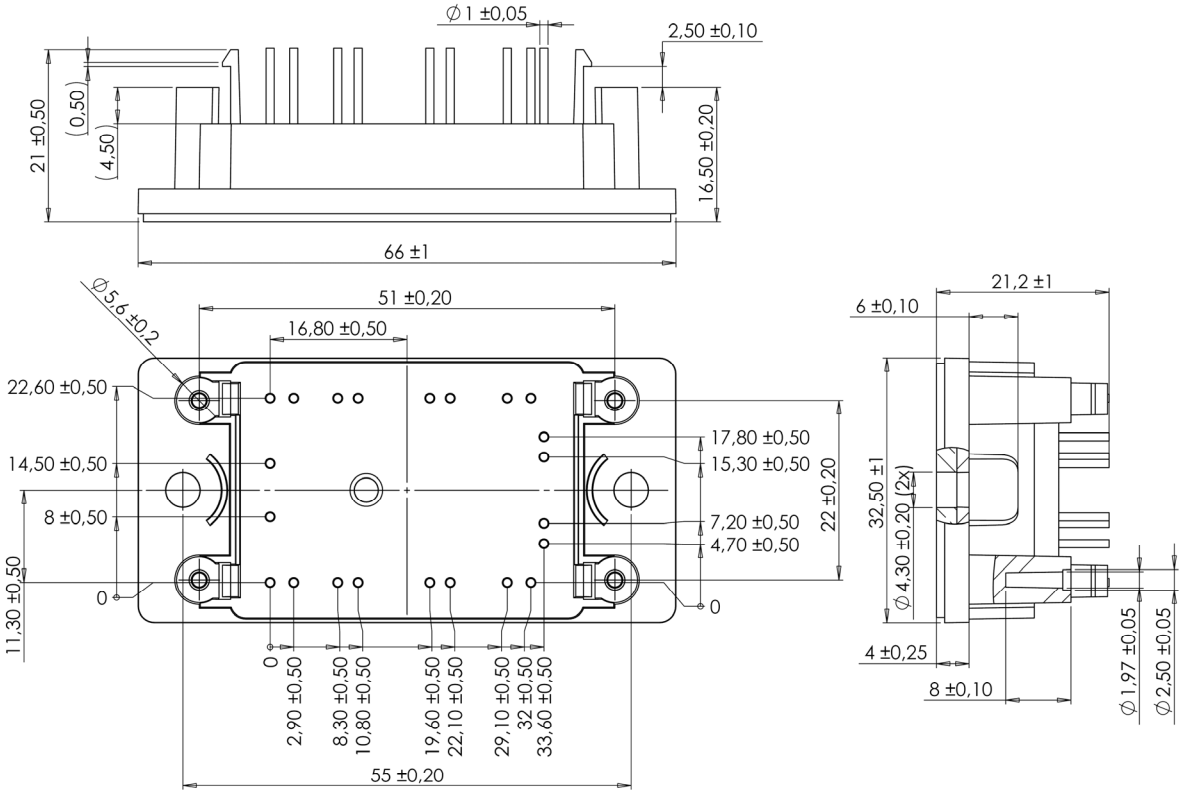
$$R_T = \frac{R_{25}}{\exp\left[B_{25/100}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

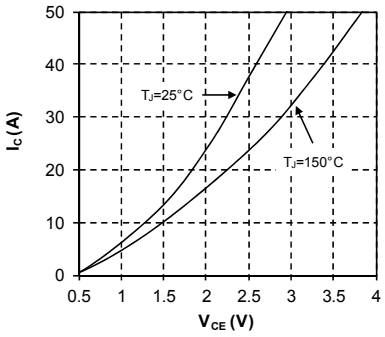
Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

package outline (dimensions in mm)

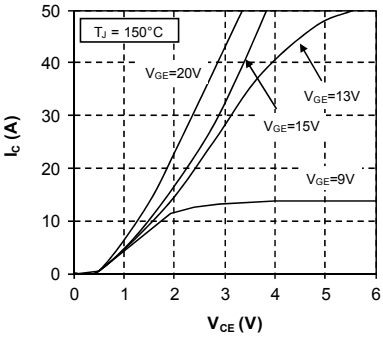


Typical Performance Curve

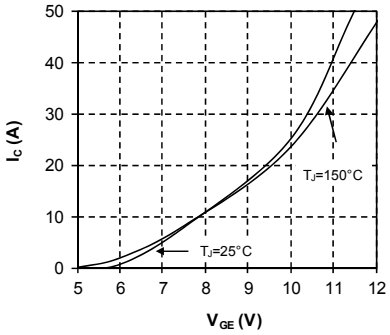
Output Characteristics (V_{GE}=15V)



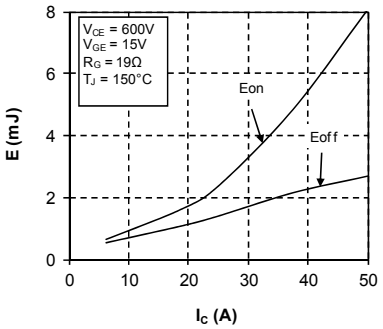
Output Characteristics



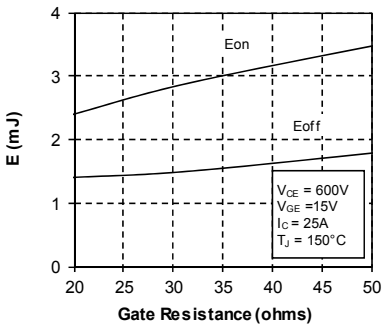
Transfert Characteristics



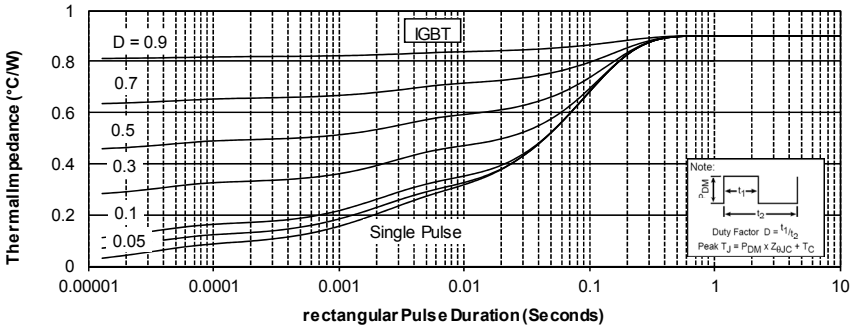
Energy losses vs Collector Current



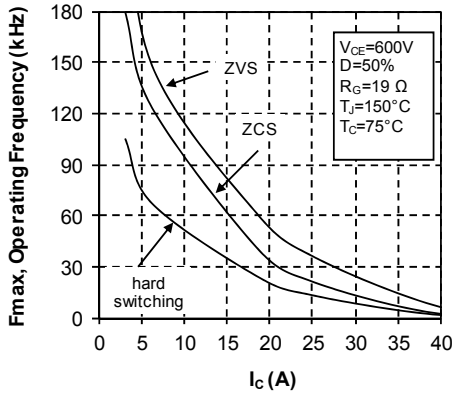
Switching Energy Losses vs Gate Resistance



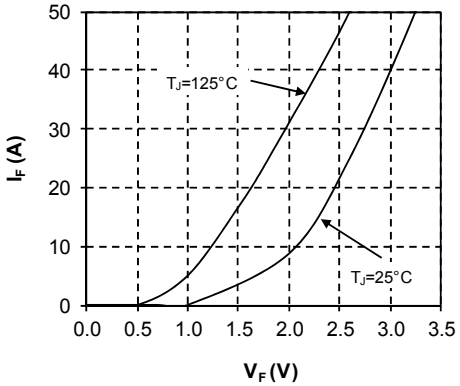
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



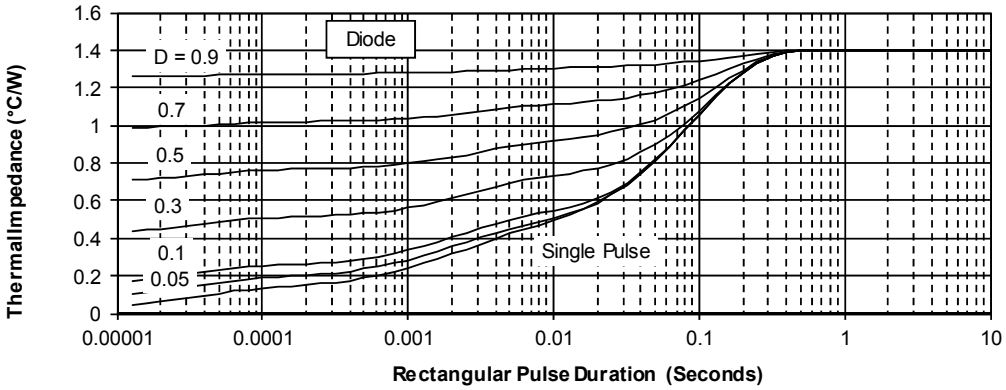
Operating Frequency vs Collector Current



Forward diode characteristic



maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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